

PRODUCT / PROCESS CHANGE NOTIFICATION

1. PCN basic data

1.1 Company	 STMicroelectronics International N.V
1.2 PCN No.	EMBEDDED PROCESSING/26/16521
1.3 Title of PCN	BOUSKOURA SO8 automotive transfer qualification: F8H P2 perimeter
1.4 Product Category	Automotive F8H EEPROM products in SO8N
1.5 Issue date	2026-09-01

2. PCN Team

2.1 Contact supplier	
2.1.1 Name	KRISZTINA NEMETH
2.1.2 Phone	+49 8946006
2.1.3 Email	krisztina.nemeth@st.com
2.2 Change responsibility	
2.2.1 Product Manager	David RICHETTO
2.1.2 Marketing Manager	Sylvain FIDELIS
2.1.3 Quality Manager	Mickael DENAIS-ALLICHON

3. Change

3.1 Category	3.2 Type of change	3.3 Manufacturing Location
Transfer	Product transfer from one site to another site, even if test or process line is qualified	N/A

4. Description of change

	Old	New
4.1 Description	The Automotive EEPROM processed in CMOS F8H and currently assembled & tested at ST Shenzhen (China)...	...will be also assembled & tested at ST Bouskoura (Morocco). The products will be assembled with Copper wires, while with Gold wires at ST Shenzhen.
4.2 Anticipated Impact on form,fit, function, quality, reliability or processability?	- Form: Marking change - Fit: No change - Function: No change	

5. Reason / motivation for change

5.1 Motivation	The strategy of the STMicroelectronics CS EEPROM division is to support our customers on products and service quality on a long-term basis. In line with this commitment, the qualification of the ST Bouskoura (Morocco) back-end assembly & test site as a second source will allow us to increase supply chain capacity and flexibility.
5.2 Customer Benefit	DOUBLE SOURCING

6. Marking of parts / traceability of change

6.1 Description	N/A
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7. Timing / schedule

7.1 Date of qualification results	2026-08-31
7.2 Intended start of delivery	2027-03-03
7.3 Qualification sample available?	Upon Request

8. Qualification / Validation

8.1 Description	16521 Qual report F8H SO8N Auto BSK - RRCS2403.pdf		
8.2 Qualification report and qualification results	Available (see attachment)	Issue Date	2026-09-01

9. Attachments (additional documentations)
16521 Public product.pdf 16521 BOUSKOURA SO8 AUTO F8H.pdf 16521 Qual report F8H SO8N Auto BSK - RRCS2403.pdf

10. Affected parts		
10. 1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
	M24512-DRMN3TP/K	
	M24C64-DRMN3TP/K	
	M95128-DRMN3TP/K	
	M95256-DRMN3TP/K	
	M95320-DRMN3TP/K	
	M95512-DRMN3TP/K	
	M95640-DRMN3TP/K	

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Public Products List

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PCN Title : BOUSKOURA SO8 automotive transfer qualification: F8H P2 perimeter

PCN Reference : EMBEDDED PROCESSING/26/16521

Subject : Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

M95320-DRMN3TP/K	M95256-DRMN3TP/K	M95512-DRMN3TP/K
M95640-DRMN3TP/K	M95128-DRMN3TP/K	M24C64-DRMN3TP/K
M24512-DRMN3TP/K		

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**ST Bouskoura additional back-end qualification
for Automotive F8H EEPROM in SO8N**

What is the change?

The Automotive EEPROM processed in CMOS F8H and currently assembled & tested at ST Shenzhen (China) will be also **assembled & tested** at **ST Bouskoura (Morocco)**.

The products will be assembled with Copper wires, while with Gold wires at ST Shenzhen.

Why?

The strategy of the STMicroelectronics Connected Security division is to support our customers on products and service quality on a long-term basis. In line with this commitment, the qualification of the ST Bouskoura (Morocco) back-end assembly & test site as a second source will allow us to increase supply chain capacity and flexibility.

When?

Shipments will start from Week 10 / 2027 or earlier on customer agreement.

How will the change be qualified?

This change is qualified using the standard STMicroelectronics Corporate Procedures for Quality and Reliability.

Report RRCS2403 is available.

What is the impact of the change?

- **Form:** Marking change
- **Fit:** No change
- **Function:** No change

- **BOX LABEL MARKING**

On the BOX LABEL, the difference is visible inside the **Finished Good Part Number** where the “**Assembly plant**” identifier is “**M**” for products assembled & tested at the **additional ST Bouskoura (Morocco)**, this identifier being “**H**” for current ST Shenzhen (China).

STMicroelectronics	Manufactured under patents or patents pending	
	Country Of Origin: France	
	Pb-free	2 nd Level Interconnect
	MSL: 1	NOT MOISTURE SENSITIVE
	PBT: 260 °C Category: e4 ECOPACK2/ROHS	
	TYPE: M95256-DRMN3TP/K M95256DRMN3TPKMA	
	Total Qty:	2500
	Trace Codes	CZYWWL
	Marking	95256RT
	Bulk ID	X0X00XXX0000
		
Please provide the bulk ID for any inquiry		
iHT (China) back-end second source qualification for low densities I²C EEPROM in SO8N package		

Assembly identifier:

- “**M**” for ST Bouskoura (Morocco)
- “**H**” for current ST Shenzhen (China)

How can the change be seen?

- DEVICE MARKING

The difference is visible inside the trace code (*PYWWT*) where the first digit “*P*” for the **assembly plant** identifier is “**Z**” for the **additional ST Bouskoura (Morocco) assembly & test**, this identifier being “**K**” for the current ST Shenzhen (China).

ST Bouskoura
(Morocco)

ST Shenzhen
(China)



P = Assembly plant
Y = Last digit of the Year of Assembly
WW = Assembly Week
T = Process technology code/ Wafer Fab ID

Appendix A- Product Change Information

Product family / Commercial products:	Automotive F8H EEPROM products in SO8N
Customer(s):	All
Type of change:	Additional back-end site
Reason for the change:	Additional sourcing
Description of the change:	ST Bouskoura (Morocco) additional back-end to current ST Shenzhen (China).
Forecast date of the change: (Notification to customer)	Week 36 / 2026
Forecast date of <u>Qualification samples</u> availability for customer(s):	Available
<u>Qualification Report</u> availability:	Reliability Evaluation Report RRCS2403 is available.
Marking to identify the changed product:	Assembly plant identifier “Z” in trace code.
Description of the qualification program:	Standard ST Microelectronics Corporate Procedures for Quality and Reliability
Estimated date of first shipment:	Week 10 / 2027 or earlier on customer agreement

Appendix B: Involved products:

Commercial part number	Samples availability
M95256-DRMN3TP/K	Available
M95128-DRMN3TP/K	Week 44 / 2026
M95640-DRMN3TP/K	Week 44 / 2026
M95320-DRMN3TP/K	Week 40 / 2026
M95512-DRMN3TP/K	Week 52 / 2026
M24512-DRMN3TP/K	Week 44 / 2026
M24C64-DRMN3TP/K	Week 52 / 2026
M95640DRMN3T/KM3	Week 52 / 2026
M95256DRMN3T/KM3	Week 52 / 2026
M95512DRMN3T/KM3	Week 52 / 2026
M95320DRMN3T/KM3	Week 52 / 2026
M95128DRMN3T/KM3	Week 52 / 2026

Appendix C: BOM comparison:

	ST Bouskoura	ST Shenzhen
Leadframe	PPF 3-layer NiPdAu	PPF 3-layer NiPdAu
Molding compound	SUMITOMO G700K	SUMITOMO G700K
Glue die-attach	ABLESTIK 8601S	ABLESTIK 8601S
Wire	Cu 1.0 mil	Au 0.8 mil

[illegible]

Source Documents & Reference Documents		
Source document Title	Rev.:	Date:



Reliability Report

RRCS2403

BE transfer

F8H SO8N Automotive qualification in Bouskoura Assembly plant

General Information		Traceability	
Commercial Product	M95320-DRMN3TP/K , M95256-DRMN3TP/K M24512-DRMN3TP/K	Diffusion Plant	Rousset 8
Product Line	9532AK,9525AK, 2412AK	Assembly Plant	ST BOUSKOURA 2 - MOROCCO
Package	SO 08 .15 JEDEC	Reliability Assessment	
Silicon Technology	CMOSF8H	Pass	X
		Fail	

Release	Date	Author	Function
3.0	July 29 th 2026	Michel DERIE	CS Back-End quality Manager

DOCUMENT ACTORS:

Name	Function	Location	Date
Michel DERIE	CS Back-End quality Manager	Rousset	July 29 th 2026
Stephane Cury	CS Product Qualification and Reliability Engineer	Rousset	July 29 th 2026
Nicolas DUMONT	CS Product Qualification and Reliability Manager	Rousset	July 29 th 2026

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RELIABILITY EVALUATION OVERVIEW

• OBJECTIVE

The aim of this reliability is to qualify Bouskoura assembly site for F8H technology EEPROM ICs in SO8N package.

Scope:

- F8H technology EEPROM products with memory size between 32kbit and 512kbit
- Package SO8N for automotive grade1 applications
- Qualification of a new assembly site: Bouskoura on top of Shenzhen qualified site.

• CONCLUSION

All reliability tests have been completed with positive results. Neither functional nor parametric rejects were detected at final electrical testing.

Package oriented tests have not put in evidence any criticality.

Based on the overall results obtained, F8H technology EEPROM products with memory size between 32kbit and 512kbit assembled in SO8N package using Bouskoura plant have positively passed reliability evaluation.

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1. RELIABILITY STRATEGY

Reliability evaluation is based on the standard STMicroelectronics corporate procedures for quality and reliability, namely RELIABILITY TESTS AND CRITERIA FOR QUALIFICATION, and in compliance with the AEC Q100 and AEC Q006 international standard.

The following qualification strategy has been defined:

- Die oriented reliability tests on 3 assembly lots: 1 lot from each test vehicle 32kb, 256kb and 512kb.
- Package oriented reliability tests on 9 assembly lots: 3 lots from each test vehicle 32kb, 256kb and 512kb.

Reliability trials performed as part of this reliability evaluation are listed in test results summary in section 3, including specifications references

2. PRODUCT OR TEST VEHICLE CHARACTERISTICS

2.1. Generalities

The 9 lots used for qualification are split among 3 Test Vehicles based on die size (TV1,2,3) that allow to cover all the involved products with memory size between 32kbit and 512kbit

2.2. Traceability

2.2.1. Wafer Fab Information

Main die - S95321KN

Wafer Fab Information	
FAB1	
Wafer fab name / location	ST SAS Rousset / Rousset 8
Wafer diameter (inches)	8
Wafer thickness (µm)	280
Silicon process technology	CMOSF8H
Number of masks	26
Die finishing front side (passivation) materials	USG NitUV (HFP USG UV Nitride)
Die finishing back side Materials	RAW SILICON - BACK GRINDING
Die area (Stepping die size)	.957042 mm ² (958, 999)
Die pad size (µm)	80x80
Sawing street width (X,Y) (µm)	60,80

Main die - S95561KN

Wafer Fab Information	
FAB1	
Wafer fab name / location	ST SAS Rousset / Rousset 8
Wafer diameter (inches)	8
Wafer thickness (µm)	280
Silicon process technology	CMOSF8H
Number of masks	26
Die finishing front side (passivation) materials	USG NitUV (HFP USG UV Nitride)
Die finishing back side Materials	RAW SILICON - BACK GRINDING
Stepping die size	1.819258 mm² (1306, 1393)
Die pad size (µm)	80x80
Sawing street width (X,Y) (µm)	60,80

Main die - S95561KN

Wafer Fab Information	
FAB1	
Wafer fab name / location	ST SAS Rousset / Rousset 8
Wafer diameter (inches)	8
Wafer thickness (µm)	280
Silicon process technology	CMOSF8H
Number of masks	26
Die finishing front side (passivation) materials	USG NitUV (HFP USG UV Nitride)
Die finishing back side Materials	RAW SILICON - BACK GRINDING
Stepping die size	2.575432 mm² (1306, 1972)
Die pad size (µm)	80x80
Sawing street width (X,Y) (µm)	60,80

2.2.2.Assembly Information

Assembly Information: 32k, 256k	
Package 1: SO8N	
Assembly plant name / location	BOUSKOURA B/E / ST BOUSKOURA 2 - MOROCCO
Die sawing method	mechanical
Lead frame/Substrate material/supplier	SO 8L 85x85 SSHD
Lead frame finishing	Preplated NiPdAu
Die attach material/type(glue/film)/supplier	GLUE LOCTITE ABLESTIK
Wire bonding material/diameter	Cu 1 mils
Molding compound material/supplier/reference	RESIN SUMITOMO EME-G700KC
Package Moisture Sensitivity Level (JEDEC J-STD020D)	1

Assembly Information: 512k	
Package 2: SO8N	
Assembly plant name / location	BOUSKOURA B/E / ST BOUSKOURA 2 - MOROCCO
Die sawing method	mechanical
Lead frame/Substrate material/supplier	SO 8L 94x125 SSHD
Lead frame finishing	Preplated NiPdAu
Die attach material/type(glue/film)/supplier	GLUE LOCTITE ABLESTIK
Wire bonding material/diameter	Cu 1 mils
Molding compound material/supplier/reference	RESIN SUMITOMO EME-G700KC
Package Moisture Sensitivity Level (JEDEC J-STD020D)	1

2.2.3.Reliability testing information

Reliability Testing Information	
Reliability laboratory name / location	Grenoble Rel Lab, Rousset MDG Rel Lab

Note: ST is ISO 9001 certified. This induces certification of all internal and subcontractor labs. ST certification document can be downloaded under the following link: http://www.st.com/content/st_com/en/support/quality-and-reliability/certifications.html

3. TEST RESULTS SUMMARY

3.1. Lot information

Lot #	Diffusion Lot / Wafer ID	Assy Lot	Raw Line	Package	Test Vehicle
Lot 1	VG344517	CZ5261XGRP	BBO7*95321KN	SO8N	TV1 32kbit
Lot2	VG344517	CZ5261XGRQ	BBO7*95321KN	SO8N	TV1 32kbit
Lot 3	VG344517	CZ5261XGRR	BBO7*95321KN	SO8N	TV1 32kbit
Lot 4	VG344405	CZ5261Y6RP	BBO7*95561KN	SO8N	TV2 256kbit
Lot 5	VG344405	CZ5261Y6RQ	BBO7*95561KN	SO8N	TV2 256kbit
Lot 6	VG344405	CZ5261Y6RR	BBO7*95561KN	SO8N	TV2 256kbit
Lot 7	VG538731	CZ604FCGRP	BBO7*24121KN	SO8N	TV3 512kbit
Lot 8	VG538731	CZ604FCGRQ	BBO7*24121KN	SO8N	TV3 512kbit
Lot 9	VG538731	CZ604FCGRR	BBO7*24121KN	SO8N	TV3 512kbit

3.2. Test plan and results summary

ACCELERATED LIFETIME SIMULATION TESTS

Test code	Stress method	Stress Conditions	Lots Qty	S.S.	Total	Results/Lot Fail/S.S.	Comments:(N/A =Not Applicable)
ELFR	JESD22-A108	Ta= 150°C Duration= 48hrs ☒ Testing at Room ☒ Testing at Hot	2	800	1600	Lot 2 : 0/800 Lot 5 : 0/800 Lot 8 : 0/800	
HTOL	JESD22-A108	Ta= 150°C Duration= 1000hrs ☒ Testing at Room T° ☒ Testing at Hot ☒ Testing at Cold	2	77	154	Lot 2 : 0/77 Lot 5 : 0/77 Lot 8 : 0/77	

ACCELERATED ENVIRONMENT STRESS TESTS

Test code	Stress method	Stress Conditions	Lots Qty	S.S.	Total	Results/Lot Fail/S.S.	Comments:(N/A =Not Applicable)
PC	J-STD-020	☒ 24h bake@125°C, ☒ 3x Reflow simulation Peak Reflow Temp= 260°C ☒ TC100cy ☒ SAM after PC	9	231	2079	Lot 1 : 0/231 Lot 2 : 0/231 Lot 3 : 0/231 Lot 4 : 0/231 Lot 5 : 0/231 Lot 6 : 0/231 Lot 7 : 0/231 Lot 8 : 0/231 Lot 9 : 0/231	
HTSL	JESD22-A103	Ta= 175°C Duration= 500h, 1000h ☒ Testing at Room ☒ Testing at Hot	9	77	693	Lot 1 : 0/77 Lot 2: 0/77 Lot 3 : 0/77 Lot 4 : 0/77 Lot 5 : 0/77 Lot 6 : 0/77 Lot 7 : 0/77 Lot 8 : 0/77 Lot 9 : 0/77	
HTSL	JESD22-A103	Ta= 150°C Duration= 1000h, 2000h ☒ Testing at Room ☒ Testing at Hot	9	77	693	Lot 1 : 0/77 Lot 2: 0/77 Lot 3 : 0/77 Lot 4 : 0/77 Lot 5 : 0/77 Lot 6 : 0/77 Lot 7 : 0/77 Lot 8 : 0/77 Lot 9 : 0/77	
TC	JESD22-A104	Ta= -65/+150°C, 2cy/h Duration = 500cy, 1000cy ☒ After PC ☒ Testing at Room ☒ Testing at Hot ☒ SAM 22u after 500cy, 1000cy	9	77	693	Lot 1 : 0/77 Lot 2: 0/77 Lot 3 : 0/77 Lot 4 : 0/77 Lot 5 : 0/77 Lot 6 : 0/77 Lot 7 : 0/77 Lot 8 : 0/77 Lot 9 : 0/77	SAM after 500cy, 1000cy: PASS
HAST	JESD22-A110	Ta=130°C/85%RH + bias Duration= 96h, 192h ☒ After PC ☒ Testing at Room ☒ Testing at Hot ☒ SAM 22u after 96h, 192h	9	77	693	Lot 1 : 0/77 Lot 2: 0/77 Lot 3 : 0/77 Lot 4 : 0/77 Lot 5 : 0/77 Lot 6 : 0/77 Lot 7 : 0/77 Lot 8 : 0/77 Lot 9 : 0/77	SAM after HAST 96h, 192h: PASS
UHAST	JESD22-A118	Ta=130°C/85%R Duration= 96h, 192h ☒ After PC ☒ Testing at Room T°	9	77	693	Lot 1 : 0/77 Lot 2: 0/77 Lot 3 : 0/77 Lot 4 : 0/77 Lot 5 : 0/77 Lot 6 : 0/77 Lot 7 : 0/77 Lot 8 : 0/77 Lot 9 : 0/77	

Electrical Verification Tests

Test code	Stress method	Stress Conditions	Lots Qty	S.S.	Total	Results/Lot Fail/S.S.	Comments:(N/A =Not Applicable)
CDM	JS-002	3u/ voltage: 250, to 1500V by step of 250V total 18u	3	18	54	Lot 1 : 0/18 Lot 6 : 0/18 Lot 8 : 0/18	Gating= 500V

Package Assembly Integrity Tests

Test code	Stress method	Test Conditions	Lots Qty	S.S.	Total	Results/Lot Fail/S.S.	Comments:(N/A =Not Applicable)
PD	Internal	Check physical dimensions against POA	9	30	180	Lot 1 : PASS Lot 2 : PASS Lot 3 : PASS Lot 4 : PASS Lot 5 : PASS Lot 6 : PASS Lot 7 : PASS Lot 8 : PASS Lot 9 : PASS	
CA	Cross section AEC Q006	☒ Perform after TC 500cy, 1000cy ☒ Perform after HAST 96h, 192h ☒ Perform after HTSL 150°C 1000h, 2000h	9	1	9	Lot 1 : PASS Lot 2 : PASS Lot 3 : PASS Lot 4 : PASS Lot 5 : PASS Lot 6 : PASS Lot 7 : PASS Lot 8 : PASS Lot 9 : PASS	
SD	J-STD-002D	2 conditions: ☒ Dry (150°C,8H) SnAgCu ☒ Steam (85 °C/85%RH,8H) SnAgCu	9	20	180	Lot 1 : PASS Lot 2 : PASS Lot 3 : PASS Lot 4 : PASS Lot 5 : PASS Lot 6 : PASS Lot 7 : PASS Lot 8 : PASS Lot 9 : PASS	
WBP	MIL-STD883 Method 2011 AEC Q003 AEC Q006	EQUIPMENT: Dage BT4000 SAMPLING: 30 wires / 5 units (6 wires /unit) ☒ Testing at T0 after package opening	9	30	180	Lot 1 : PASS Lot 2 : PASS Lot 3 : PASS Lot 4 : PASS Lot 5 : PASS Lot 6 : PASS Lot 7 : PASS Lot 8 : PASS Lot 9 : PASS	

Reliability Report

WBP	MIL-STD883 Method 2011 AEC Q003 AEC Q006	EQUIPMENT: Dage BT4000 SAMPLING: 30 wires / 5 units (6 wires /unit) ☒ Testing after TC 500cy, 1000cy ☒ Testing after HAST 96h, 192h	9	3	27	Lot 1 : PASS Lot 2 : PASS Lot 3 : PASS Lot 4 : PASS Lot 5 : PASS Lot 6 : PASS Lot 7 : PASS Lot 8 : PASS Lot 9 : PASS	
WBS	AECQ100-001, AEC Q003 AEC Q006	EQUIPMENT: Dage BT4000 SAMPLING: 30 wires / 5 units (6 wires /unit) ☒ Testing at T0 after package opening	9	30	270	Lot 1 : PASS Lot 2 : PASS Lot 3 : PASS Lot 4 : PASS Lot 5 : PASS Lot 6 : PASS Lot 7 : PASS Lot 8 : PASS Lot 9 : PASS	
WBS	AECQ100-001, AEC Q003 AEC Q006	EQUIPMENT: Dage BT4000 SAMPLING: 30 wires / 5 units (6 wires /unit) ☒ Testing after TC 500cy, 1000cy ☒ Testing after HAST 96h, 192h	9	30	270	Lot 1 : PASS Lot 2 : PASS Lot 3 : PASS Lot 4 : PASS Lot 5 : PASS Lot 6 : PASS Lot 7 : PASS Lot 8 : PASS Lot 9 : PASS	

Note: Test method revision reference is the one active at the date of reliability trial execution.

4. APPLICABLE AND REFERENCE DOCUMENTS

Reference	Short description
JESD47	Stress-Test-Driven Qualification of Integrated Circuits
AEC Q100	Failure mechanism based stress test qualification for integrated circuits in automotive applications
AEC Q006	Qualification requirements for components using Copper (Cu) wire interconnections

5. GLOSSARY

CDM	Electrostatic Discharge - Charged device model
ELFR	Early life failure rate
HAST	Biased HAST (Highly Accelerated Stress Test)
HBM	Electrostatic Discharge - Human Body Model
HTOL	High Temperature Operating Life
HTSL	High Temperature Storage Life
PC	Preconditioning
TC	Temperature Cycling
THB	Temperature Humidity Bias
UHAIST	Unbiased HAST (Highly Accelerated Stress Test)
PD	Physical dimensions check
SD	Solderability
WBP	Wire Bond pull test
WBS	Wire Bond shear test

6. REVISION HISTORY

Release	Date	Description
1.0	Dec 8 th 2025	Initial release
2.0	March 9 th 2026	Updated with latest results
3.0	July 29 th 2026	Including full range of products and all results

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